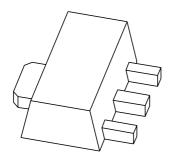
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## BST39; BST40 NPN high-voltage transistors

Product specification Supersedes data of 2000 Jul 03

2004 Dec 14





## **NPN** high-voltage transistors

**BST39; BST40** 

#### **FEATURES**

- Low current (max. 100 mA)
- High voltage (max. 350 V).

#### **APPLICATIONS**

• General purpose switching and amplification.

#### **DESCRIPTION**

NPN high-voltage transistor in a SOT89 plastic package. PNP complements: BST15 and BST16.

#### **MARKING**

TYPE NUMBER	MARKING CODE
BST39	AT1
BST40	AT2

#### **PINNING**

PIN	DESCRIPTION	
1	emitter	
2	collector	
3	base	

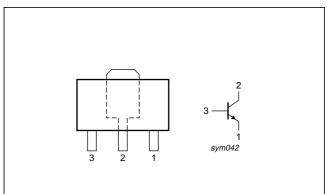


Fig.1 Simplified outline (SOT89) and symbol.

#### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE			
TIPE NUMBER	NAME DESCRIPTION		VERSION	
BST39	SC-62	plastic surface mounted package; collector pad for good heat	SOT89	
BST40	transfer; 3 leads			

## NPN high-voltage transistors

**BST39**; **BST40** 

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BST39		_	400	V
	BST40		_	300	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BST39		_	350	V
	BST40		_	250	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	200	mA
I <sub>BM</sub>	peak base current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1.3	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

#### Note

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	96	K/W
$R_{th(j-s)}$	thermal resistance from junction to soldering point		16	K/W

#### Note

#### **CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 300 V	_	20	nA
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 5 V	_	100	nA
h <sub>FE</sub>	DC current gain	$I_C = 20 \text{ mA}; V_{CE} = 10 \text{ V}$	40	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 4 \text{ mA}$	_	500	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V}; f = 1 \text{ MHz}$	_	2	pF
f <sub>T</sub>	transition frequency	$I_C = 10 \text{ mA}$ ; $V_{CE} = 10 \text{ V}$ ; $f = 100 \text{ MHz}$	70	_	MHz

<sup>1.</sup> Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

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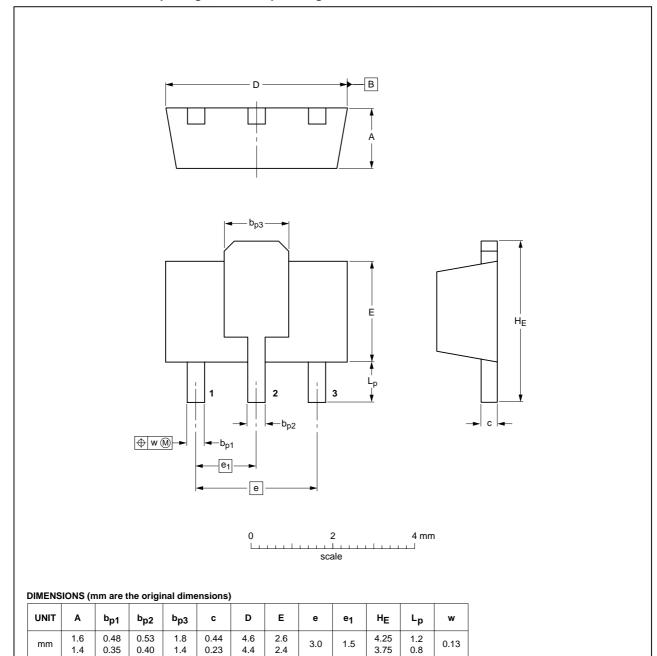
## NPN high-voltage transistors

**BST39**; **BST40** 

#### **PACKAGE OUTLINE**

#### Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION IEC		JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT89		TO-243	SC-62			<del>99-09-13</del> 04-08-03

### NPN high-voltage transistors

**BST39**; **BST40** 

#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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